

<b>INFORMATION DISCLOSURE STATEMENT PTO-1449</b>	Atty. Docket No. 040153	Serial No. <sup>W/813,085</sup> <del>New Application</del>
	Applicant(s): Toshihide KIKKAWA	
	Filing Date: March 31, 2004	Group Art Unit: <sup>2811</sup> <del>Not Yet Assigned</del>

### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					

### FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
_____	AC		
_____	AD		
_____	AE		
_____	AF		
_____	AG		

### OTHER DOCUMENTS

<u>✓</u>	AH	Patent Abstracts of Japan, Publication Number 2001-185717, dated July 6, 2001.
<u>✓</u>	AI	Patent Abstracts of Japan, Publication Number 2002-359256, dated December 13, 2002.
<u>✓</u>	AJ	T. Hashizume, et al.; "Discrete surface state related to nitrogen-vacancy defect on plasma-treated GaN surfaces"; <i>Applied Physics Letters</i> ; Vol. 80; No. 24; June 17, 2002; pp. 4564-4566.
Examiner	HUNG JU	Date Considered W 11/05